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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









TS13002A

High Voltage NPN Transistor



TO-92



Pin Definition:

- 1. Emitter
- 2. Collector
- 3. Base

PRODUCT SUMMARY

BV _{CEO}	400V
BV _{CBO}	700V
Ic	0.3A
V _{CE(SAT)}	$1.5V @ I_C / I_B = 200mA / 20mA$

Features

- High Voltage
- High Speed Switching

Structure

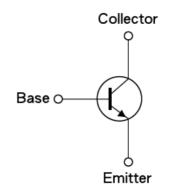
- Silicon Triple Diffused Type
- NPN Silicon Transistor

Ordering Information

Part No.	Package	Packing	
TS13002ACT B0G	TO-92	1Kpcs / Bulk	
TS13002ACT A3G	TO-92	2Kpcs / Ammo	

Note: "G" denote for Green Product

Block Diagram



Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Collector-Base Voltage		$V_{\sf CBO}$	700V	V	
Collector-Emitter Voltage		$V_{\sf CEO}$	400V	V	
Emitter-Base Voltage		V_{EBO}	9	V	
Collector Current	DC		0.3		
	Pulse	Ic	0.5	Α	
Collector Power Dissipation		P_{D}	0.6	W	
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit	
Junction to Ambient Thermal Resistance	RO _{JA}	122	°C/W	



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Pb RoHS COMPLIANCE

Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Collector-Base Voltage	$I_{C} = 1 \text{mA}, I_{B} = 0$	BV _{CBO}	700			V
Collector-Emitter Breakdown Voltage	$I_C = 10 \text{mA}, I_E = 0$	BV _{CEO}	400			V
Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	BV_{EBO}	9			V
Collector Cutoff Current	$V_{CB} = 700V, I_{E} = 0$	I _{CBO}			1	uA
Emitter Cutoff Current	$V_{EB} = 7V, I_{C} = 0$	I _{EBO}			1	uA
	$I_{C} / I_{B} = 50 \text{mA} / 10 \text{mA}$	V _{CE(SAT)1}		0.2	0.4	
Collector-Emitter Saturation Voltage	$I_{C} / I_{B} = 100 \text{mA} / 10 \text{mA}$	V _{CE(SAT)2}		0.45	1	V
Base-Emitter Saturation Voltage	$I_C / I_B = 200 \text{mA} / 20 \text{mA}$	V _{CE(SAT)3}		1	1.5	
Page Emitter Seturation Voltage	$I_{C} / I_{B} = 50 \text{mA} / 10 \text{mA}$	$V_{BE(SAT)1}$			1	V
Base-Emiller Saturation voltage	$I_{C} / I_{B} = 100 \text{mA} / 10 \text{mA}$	V _{BE(SAT)2}			1.2	V
	$V_{CE} = 10V, I_{C} = 10mA$	h _{FE} 1	15		40	
DC Current Gain	$V_{CE} = 10V, I_{C} = 100mA$	h _{FE} 2	25		40	
	$V_{CE} = 10V, I_{C} = 280mA$	h _{FE} 3	12		24	
Dynamic						
Frequency	$V_{CE} = 10V, I_{C} = 0.1A$	f _T	4			MHz
Output Capacitance	$V_{CB} = 10V, f = 0.1MHz$	Cob		21		pF
Resistive Load Switching Time (Ratings)						
Rise Time	$V_{CC} = 125V, I_C = 100mA,$	t _r		1.1		uS
Storage Time	$I_{B1} = I_{B2} = 20\text{mA},$ $I_{D} = 25\text{uS}$	t _{STG}		2	4	uS
Fall Time	Duty Cycle ≤1%	t _f		0.2	0.7	uS

Note : pulse test: pulse width \leq 5mS, duty cycle \leq 10%





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Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



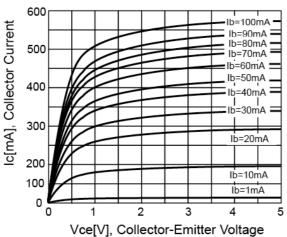


Figure 3. V_{CE(SAT)} v.s. V_{BE(SAT)}

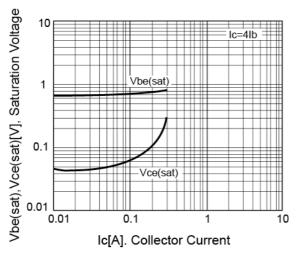


Figure 5. Reverse Bias SOA

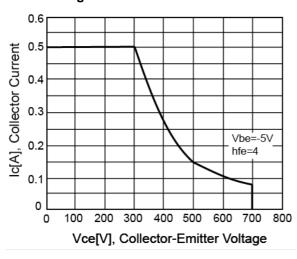


Figure 2. DC Current Gain

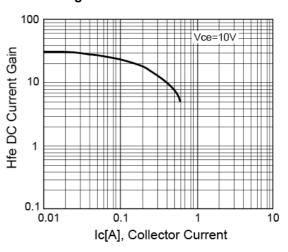


Figure 4. Power Derating

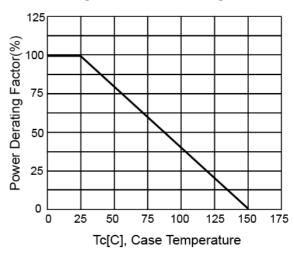
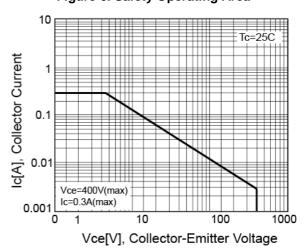


Figure 6. Safety Operating Area

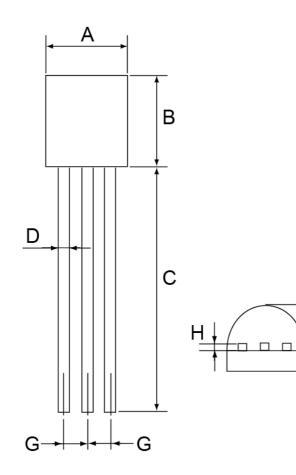






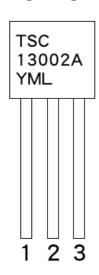
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TO-92 Mechanical Drawing



TO-92 DIMENSION						
DIM	MILLIMETERS		INCHES			
DIM	MIN	MAX	MIN	MAX		
Α	4.30	4.70	0.169	0.185		
В	4.30	4.70	0.169	0.185		
С	13.53	13.53 (typ)		0.532 (typ)		
D	0.39	0.49	0.015	0.019		
Е	1.18	1.28	0.046	0.050		
F	3.30	3.70	0.130	0.146		
G	1.27	1.31	0.050	0.051		
Н	0.33	0.43	0.013	0.017		

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S =May T =Jun U =Jul V =Aug W =Sep X =Oct Y =Nov Z =Dec

L = Lot Code



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